	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 6005270 A	19991221	29	Semiconductor nonvolatile memory device and method of production of same	257/315	257/20; 257/30; 257/316; 257/321; 257/337; 257/390; 257/401; 257/43	Noguchi, Takashi
2	US 6137120 A	20001024	301	Semiconductor device and method of fabricating the same	257/66	257/347; 257/350; 257/57; 257/72	Shindo, Masahiro et al.
3	US 5818083 A	19981006	15	Semiconductor memory device having a floating gate	257/321	257/66	Ito, Takashi
4	US 5808336 A	19980915	35	Storage device	257/315	257/369; 257/80	Miyawaki, Mamoru
5	US 5279981 A	19940118	16	Method of reducing the trap density of an oxide film for application to fabricating a nonvolatile memory cell	438/264	438/787; 438/910	Fukatsu, Shigemitsu et al.
6	US 5982462 A	19991109	16	Inverse stagger or planar type thin-film transistor device and liquid-crystal display apparatus having floating gate electrode which is capacitively coupled with one or more input electrodes	349/43	257/59; 349/151; 349/46	Nakano, Akira et al.
7	US 5648277 A	19970715	18	Method of manufacturing a semiconductor device	438/151	438/163; 438/517	Zhang, Hongyong et al.

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5656845 A	19970812	11	EEPROM on insulator	257/347	257/315	Akbar, Shahzad

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